Calibrating energy scale of SuperCDMS Si HVeV detectors in keV range and

studying the Compton Steps



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Abstract

We present an overview of SuperCDMS (Super Cryogenic Dark Matter Search) HVeV (High Voltage eV resolution) detectors, 1 g Si High Voltage (HV) detectors, that have ~eV resolution and dynamic range up to ~keV. Using LED and ¹³⁷Cs data, we aim to calibrate the energy scale of the detectors up to the keV range and study the Compton steps. The understanding of Compton steps for these detectors will be used to calibrate the big SuperCDMS HV detectors for the 2nd generation SuperCDMS experiment at SNOLAB.

1. Dark matter search experiments

Astrophysical observations support existence of dark matter.

Known properties

- Interacts gravitationally
- Non-relativistic / Cold
- **Electrically neutral**
- Very weak interaction crosssection
- $\psi \rightarrow$ Standard model particle
- $\chi \rightarrow \mathbf{Dark}$ matter particle
- Collider search $(\psi\psi \to \chi\chi)$
- Indirect search $(\chi \chi \rightarrow \psi \psi)$
- Direct search $(\psi \chi \rightarrow \psi \chi)$



2. Detection principle of SuperCDMS detectors

Energy deposition Drifting of ions through the crystal due to applied bias from incoming particles voltage

3eV/3.8 eV energy is needed for 1 e⁻h⁺

• NTL⁽¹⁾ phonons are created during drifting though the

Transition edge sensor (TES) as the phonon sensor

HDMS

GENIUS

IGEX

• Thin superconducting film

3. NEXUS@FNAL

Northweste EXUS@FNAL: 107 meter underground. Sermilab @ENERGY **NEXUS (SuperCDMS Test facility):** Outer channel • 0.93g (~1g) Si HVeV detector with ~eV resolution



- Detectors: NFE, NFH, NFC1 & NFC2
- Single charge sensitive, eV scale threshold with keV scale

Sensitive to sub-GeV dark matter particles





5. Expected features from Geant4 simulation

Source information: ¹³⁷Cs \longrightarrow ¹³⁷Ba + γ (662 keV) + β^- **Dominating interaction process: Compton scattering** Simulating platform: SuperSim-V09-01-00, Genat4-10.06.p03

¹³⁷Cs photo peak (662 keV): Full gamma energy deposition ¹³⁷Cs Compton edge (477 keV): Backscattered gamma

Cu X ray peak (8.1 keV): Due to the Cu housing Compton steps: Due to electronic shell structure of Si



Compton step

- At energies comparable to the atomic binding energies, the free electron approximation fails
- If $E < E_{n,l}$ the energy spectrum forms a step
- The relative height of each step is given by the ratio of the electrons in each shell to the total number of available electrons
- Position of Compton steps in the energy spectrum depends on the atomic shell energies; hence it is material dependent

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Si Shell	Quantum number (n,l)	E _{n,I} (keV)	Shell e ⁻
K	(1,0)	1.839	2
L1	(2,0)	0.150	2
L _{2,3}	(2,1)	0.099	6







Apply cuts to remove bad pulses / poorly reconstructed events from the science data Optimize the Matched Filter (MF) integral, a hybrid energy estimator of OFL and Integral Study OV and HV (100V) data and look for K shell (1.8 keV) and L shell (150 eV) Compton steps Perform Energy calibration at low energy ranges in both 0V and HV bias modes using the Compton

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